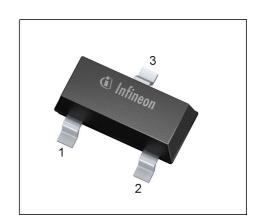


Low Noise Silicon Bipolar RF Transistor

- High linearity low noise RF transistor
- 22 dBm OP1dB and 31 dBm OIP3
 @ 900 MHz, 8 V, 70 mA
- For UHF / VHF applications
- Driver for multistage amplifiers
- For linear broadband and antenna amplifiers
- Collector design supports 5 V supply voltage
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR106	R7s	1=B	2=E	3=C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage,	$V_{\sf CEO}$		V
$T_A = 25^{\circ}C$		16	
$T_{A} = -55^{\circ}C$		15	
Collector-emitter voltage	V _{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V _{EBO}	3	
Collector current	$I_{\mathbb{C}}$	210	mA
Base current	l _B	21	
Total power dissipation ¹⁾	P _{tot}	700	mW
<i>T</i> _S ≤ 76 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T_{Stq}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	105	K/W

 $^{{}^{1}}T_{\rm S}$ is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	15	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0	, ,				
Collector-emitter cutoff current	I _{CES}				μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$		-	-	1	
$V_{CE} = 10 \text{ V}, V_{BE} = 0$		-	0.001	0.03	
Collector-base cutoff current	I _{CBO}	-	1	30	nA
$V_{CB} = 10 \text{ V}, I_{E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	1	30	
$V_{\rm EB} = 2 \text{ V}, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Transition frequency	f_{T}	3.5	5	-	GHz	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz						
Collector-base capacitance	C _{cb}	-	0.85	1.2	pF	
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,						
emitter grounded						
Collector emitter capacitance	C _{ce}	-	0.27	-		
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,						
base grounded						
Emitter-base capacitance	C _{eb}	-	3.9	-		
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,						
collector grounded						
Minimum noise figure	<i>NF</i> _{min}				dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
f = 900 MHz		-	1.8	-		
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
f = 1.8 GHz		-	3	-		



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	j)				
Power gain, maximum available ¹⁾	G _{ma}				dB
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz		-	13	-	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz		-	8.5	-	
Transducer gain	$ S_{21e} ^2$				dB
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	10.5	-	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz		-	5	-	
Third order intercept point at output ²⁾	IP ₃	-	31	-	dBm
$V_{CE} = 8 \text{ V}, I_{C} = 70 \text{ mA}, f = 0.9 \text{ GHz},$					
$Z_{S}=Z_{L}=50\Omega$					
1dB compression point	P _{-1dB}	-	22	-	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ =50 Ω ,					
f = 0.9 GHz					

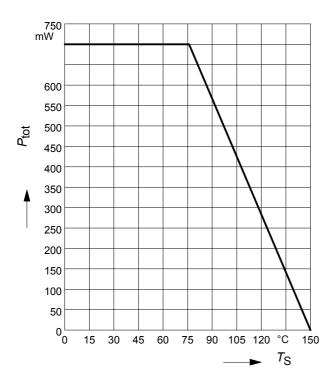
 $^{{}^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$

 $^{{}^2\}emph{IP}_3$ value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$





SPICE GP Model

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

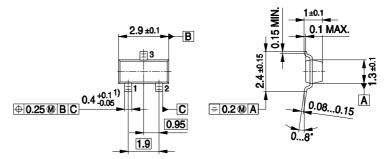
Please consult our website and download the latest versions before actually starting your design.

6



Package Outline

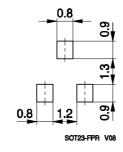




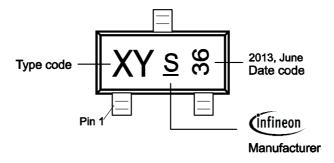
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

Foot Print

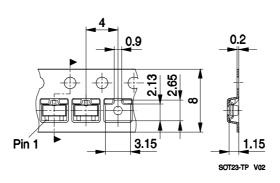


Marking Layout



Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel





Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<www.infineon.com>).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon Technologies(英飞凌)